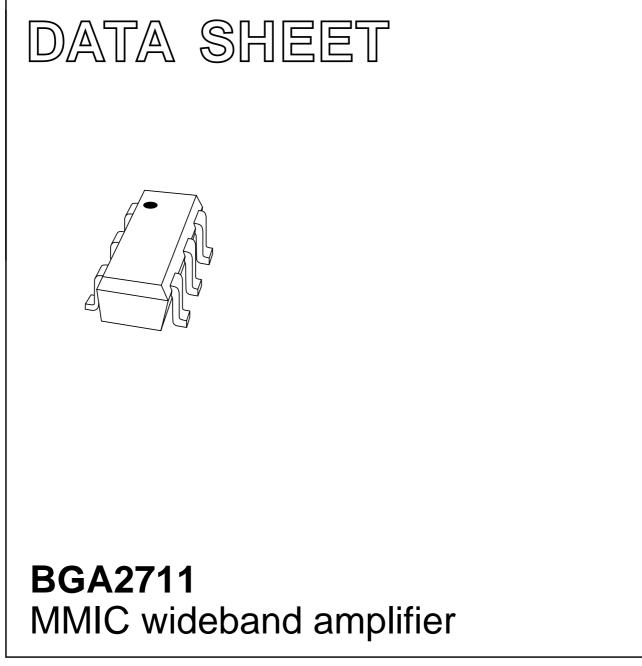
DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 2001 Apr 04 2001 Oct 19



FEATURES

- Internally matched to 50 Ω
- · Very wide frequency range
- · Very flat gain
- Unconditionally stable.

APPLICATIONS

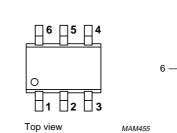
- · Cable systems
- · LNB IF amplifiers
- · General purpose
- ISM.

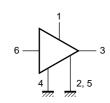
DESCRIPTION

Silicon Monolithic Microwave Integrated Circuit (MMIC) wideband amplifier with internal matching circuit in a 6-pin SOT363 SMD plastic package.

PINNING

PIN	DESCRIPTION			
1	V _S			
2, 5	GND2			
3	RF out			
4	GND1			
6	RF in			





Marking code: G2-.

Fig.1 Simplified outline (SOT363) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V _S	DC supply voltage		5	6	V
I _S	DC supply current		12.6	-	mA
s ₂₁ ²	insertion power gain	f = 1 GHz	13.1	-	dB
NF	noise figure	f = 1 GHz	4.8	_	dB
P _{L(sat)}	saturated load power	f = 1 GHz	2.8	_	dBm

CAUTION

This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A and SNW-FQ-302B.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Vs	DC supply voltage	RF input AC coupled	_	6	V
I _S	supply current		_	20	mA
P _{tot}	total power dissipation	$T_s \le 80 \ ^{\circ}C$	_	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	operating junction temperature		_	150	°C
PD	maximum drive power		_	10	dBm

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-s}	thermal resistance from junction to solder point	P_{tot} = 200 mW; $T_s \le 80 \ ^\circ C$	300	K/W

CHARACTERISTICS

 V_S = 5 V; I_S = 12.6 mA; f = 1 GHz; T_j = 25 $^\circ C$ unless otherwise specified.

SYMBOL PARAMETER		CONDITIONS	MIN.	TYP.	MAX.	UNIT	
I _S	supply current		10	12.6	16	mA	
s ₂₁ ²	insertion power gain	f = 1 GHz	-	13.1	-	dB	
		f = 2 GHz	-	13.9	-	dB	
R _{L IN}	return losses input	f = 1 GHz	-	11	-	dB	
		f = 2 GHz	-	10	-	dB	
R _{L OUT}	return losses output	f = 1 GHz	-	18	-	dB	
		f = 2 GHz	-	13	-	dB	
NF	noise figure	f = 1 GHz	-	4.8	-	dB	
		f = 2 GHz	-	4.8	-	dB	
BW	bandwidth	at s ₂₁ ² -3 dB below flat gain at 1 GHz	-	3.6	-	GHz	
P _{L(sat)}	saturated load power	f = 1 GHz	-	2.8	-	dBm	
		f = 2 GHz	-	0.6	-	dBm	
P _{L 1 dB}	load power	at 1 dB gain compression; f = 1 GHz	-	-0.7	-	dBm	
		at 1 dB gain compression; f = 2 GHz	-	-1.8	-	dBm	
IP3 _(in)	input intercept point	f = 1 GHz	-	-4.8	-	dBm	
· · /		f = 2 GHz	-	-8.5	-	dBm	
IP3 _(out)	output intercept point	f = 1 GHz	-	8.3	-	dBm	
. ,		f = 2 GHz	-	5.4	-	dBm	

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APPLICATION INFORMATION

Figure 2 shows a typical application circuit for the BGA2711 MMIC. The device is internally matched to 50 Ω , and therefore does not need any external matching. The value of the input and output DC blocking capacitors C2, C3 should be not more than 100 pF for applications above 100 MHz. However, when the device is operated below 100 MHz, the capacitor value should be increased.

The 22 nF supply decoupling capacitor, C1 should be located as closely as possible to the MMIC.

Separate paths must be used for the ground planes of the ground pins GND1, GND2, and these paths must be as short as possible. When using vias, use multiple vias per pin in order to limit ground path inductance.

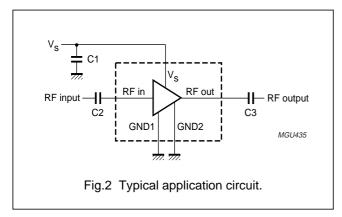
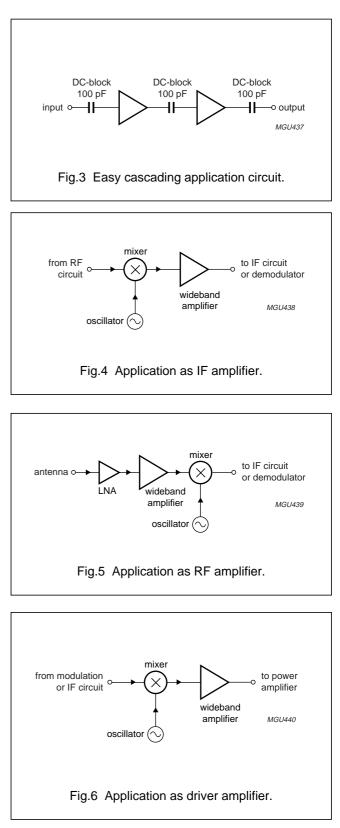


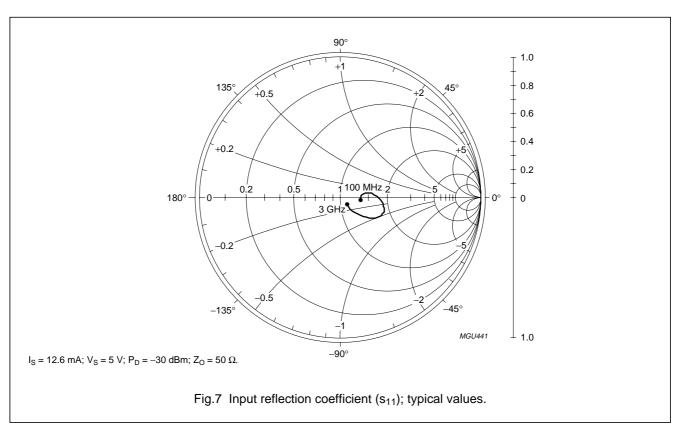
Figure 3 shows two cascaded MMICs. This configuration doubles overall gain while preserving broadband characteristics. Supply decoupling and grounding conditions for each MMIC are the same as those for the circuit of Fig.2.

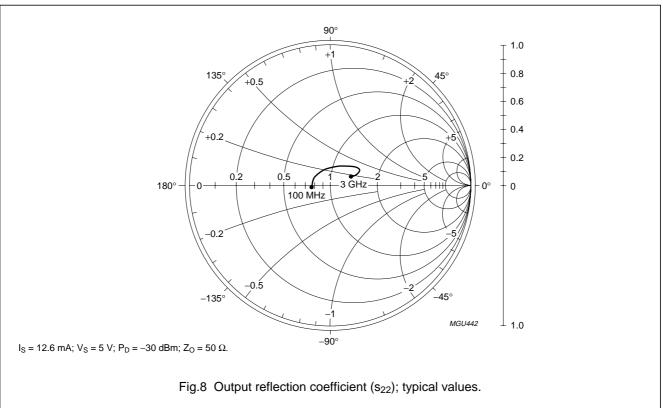
The excellent wideband characteristics of the MMIC make it and ideal building block in IF amplifier applications such as LBNs (see Fig.4).

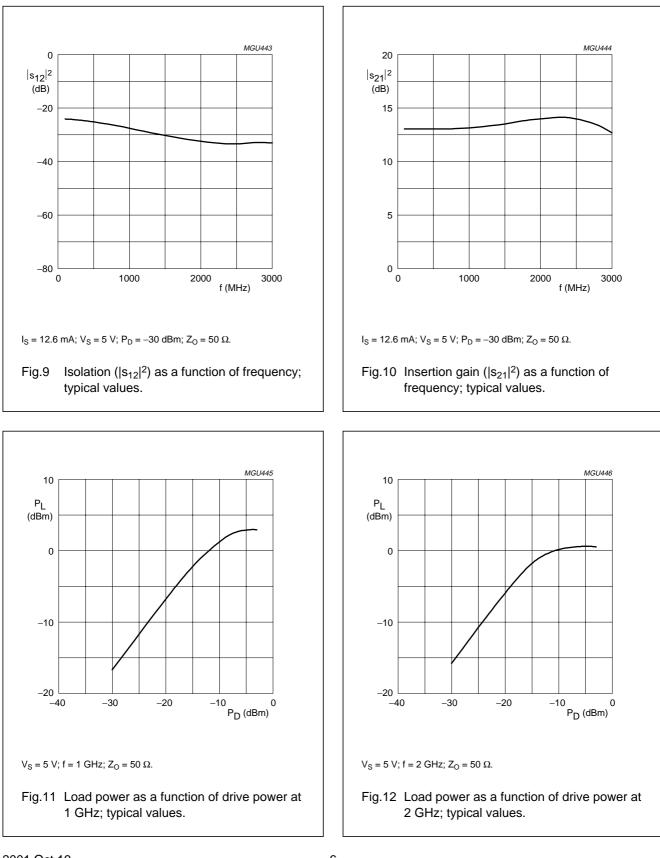
As a buffer amplifier between an LNA and a mixer in a receiver circuit, the MMIC offers an easy matching, low noise solution (see Fig.5).

In Fig.6 the MMIC is used as a driver to the power amplifier in part of a transmitter circuit. Good linear performance and matched input and output offer quick design solutions in such applications.









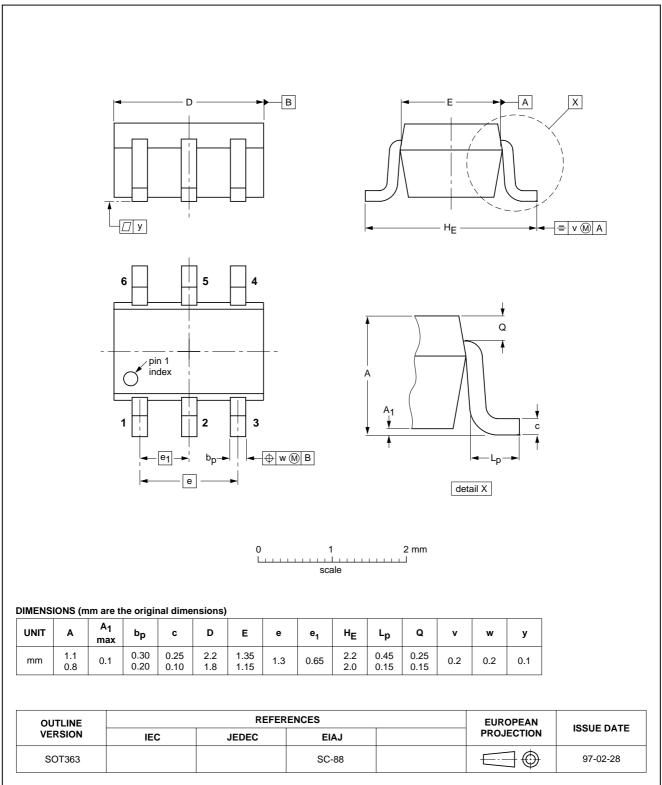
MGU448 MGU447 10 5 NF (dB) κ 8 4 6 3 4 2 2 1 0 ` 0 1000 2000 3000 0 1000 2000 3000 f (MHz) f (MHz) I_{S} = 12.6 mA; V_{S} = 5 V; Z_{O} = 50 $\Omega.$ I_{S} = 12.6 mA; V_{S} = 5 V; Z_{O} = 50 $\Omega.$ Fig.13 Noise figure as a function of frequency; Fig.14 Stability factor as a function of frequency; typical values. typical values.

Scattering parameters: I_S = 12.6 mA; P_D = -30 dBm; Z_O = 50 $\Omega;$ T_{amb} = 25 $^{\circ}\text{C}$

f S ₁₁			s ₂₁		s ₁₂		s ₂₂		
(MHz)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	
100	0.14563	-3.502	4.4867	-1.843	0.06220	-2.939	0.13029	-174.50	
200	0.15253	5.557	4.4944	-6.788	0.06117	-8.095	0.12640	169.58	
400	0.18735	10.06	4.4841	-15.22	0.05751	-16.61	0.11957	148.02	
600	0.22695	8.206	4.4862	-22.94	0.05240	-22.85	0.11288	126.58	
800	0.26122	2.635	4.4985	-30.57	0.04744	-27.72	0.11286	104.24	
1000	0.28776	-2.465	4.5390	-38.34	0.04187	-31.17	0.12236	82.570	
1200	0.30888	-8.179	4.6052	-46.14	0.03666	-32.98	0.14066	65.815	
1400	0.32055	-13.16	4.6862	-54.45	0.03251	-33.25	0.16341	53.911	
1600	0.32492	-17.85	4.7929	-63.29	0.02903	-32.38	0.18689	45.122	
1800	0.31849	-22.43	4.9219	-72.67	0.02624	-29.24	0.20662	38.894	
2000	0.30085	-26.75	4.9973	-83.08	0.02395	-26.62	0.22092	33.706	
2200	0.27106	-31.57	5.0755	-93.96	0.02228	-22.20	0.22754	29.699	
2400	0.23157	-35.78	5.0668	-106.1	0.02134	-17.95	0.22679	26.622	
2600	0.18594	-40.38	4.9143	-118.1	0.02176	-13.86	0.21806	23.868	
2800	0.13159	-44.34	4.6797	-129.6	0.02276	-12.70	0.19660	22.060	
3000	0.07266	-41.76	4.3139	-140.5	0.02241	-17.06	0.16355	22.273	

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads



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SOT363

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DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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